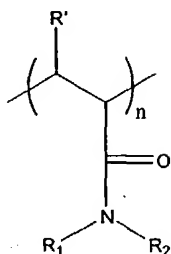


What is claimed is:

1. A photoresist overcoating composition comprising:
a solvent; and
a compound represented by Formula 1:

Formula 1



wherein

R' is H or CH₃;

R₁ and R₂ individually are H or C₁-C₃ alkyl.

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2. The photoresist overcoating composition according to claim 1,
wherein the compound of Formula 1 is poly(N,N-dimethylacrylamide).

3. The photoresist overcoating composition according to claim 1,
15 wherein the solvent is distilled water.

4. The photoresist overcoating composition according to claim 1,
wherein the compound of Formula 1 is present in an amount ranging from 1 to 30 wt%
to the solvent.

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5. A process for forming a photoresist pattern, comprises:
(a) coating a photoresist composition on an underlying layer to form a
photoresist film;
(b) coating the photoresist overcoating composition of claim 1 on the
25 photoresist film to form an overcoating film;
(c) exposing the resultant structure;
(d) baking the resultant structure; and
(e) developing the resultant structure.

6. The process according to claim 5, wherein the photoresist composition includes a chemically amplified photoresist resin.

5 7. The process according to claim 5, wherein the light source of the exposing step is selected from the group consisting of ArF(193 nm), KrF(248 nm), F₂(157 nm), EUV(13 nm), E-beam, X-ray and ion beam.